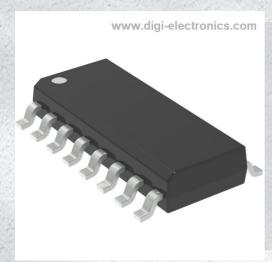


# MC74VHC139DR2 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MC74VHC139DR2-DG

Manufacturer onsemi

Manufacturer Product Number MC74VHC139DR2

Description IC DECODER/DEMUX 1X2:4 16SOIC

Detailed Description Decoder/Demultiplexer 1 x 2:4 16-SOIC



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MC74VHC139DR2	onsemi
Series:	Product Status:
74VHC	Obsolete
Туре:	Circuit:
Decoder/Demultiplexer	1 x 2:4
Independent Circuits:	Current - Output High, Low:
2	8mA, 8mA
Voltage Supply Source:	Voltage - Supply:
Single Supply	2V ~ 5.5V
Operating Temperature:	Mounting Type:
-55°C ~ 125°C	Surface Mount
Package / Case:	Supplier Device Package:
16-SOIC (0.154", 3.90mm Width)	16-SOIC
Base Product Number:	
74VHC139	

# **Environmental & Export classification**

8542.39.0001

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

# **Dual 2-to-4 Decoder/ Demultiplexer**

The MC74VHC139 is an advanced high speed CMOS 2-to-4 decoder/ demultiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled ( $\overline{E} = low$ ), it can be used for gating or as a data input for demultiplexing operations. When the enable input is held high, all four outputs are fixed high, independent of other inputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 5.0 \text{ ns (Typ)}$  at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;

Machine Model > 200 V

- Chip Complexity: 100 FETs or 25 Equivalent Gates
- Pb-Free Packages are Available\*



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## **MARKING DIAGRAMS**

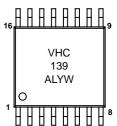


SOIC-16 **D SUFFIX** CASE 751B



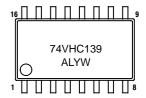
TSSOP-16 **DT SUFFIX CASE 948F** 







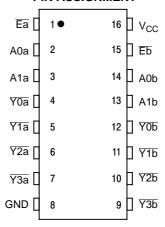
SOEIAJ-16 **M SUFFIX CASE 966** 



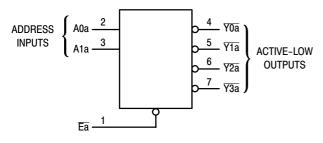
Α = Assembly Location

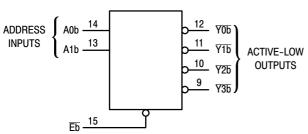
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

## **PIN ASSIGNMENT**



ORDERING INFORMATION See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.





**Table 1. FUNCTION TABLE** 

Inputs			Outputs			
E	A1	A0	Y0	<u>Y1</u>	<u>Y2</u>	<u>Y3</u>
Н	Х	Х	Н	Н	Н	Н
L	L	L	L	Н	Н	Н
L	L	Н	Н	L	Н	Н
L	Н	L	Н	Н	L	Н
L	Н	Н	Н	Н	Н	L

Figure 1. Logic Diagram

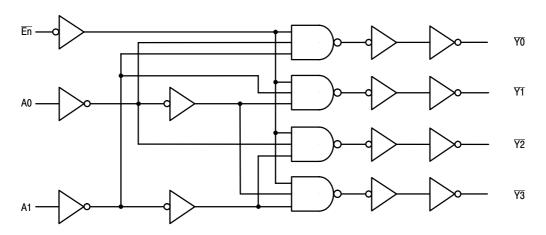


Figure 2. Expanded Logic Diagram (1/2 of Device)

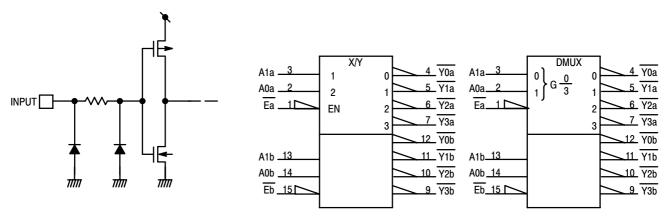


Figure 3. Input Equivalent Circuit

Figure 4. IEC Logic Diagram

#### **MAXIMUM RATINGS**

Symbol	Paramete	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>out</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input Diode Current	-20	mA	
I <sub>OK</sub>	Output Diode Current	±20	mA	
l <sub>out</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GN	ND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages <sup>†</sup> TSSOP Package <sup>†</sup>	500 450	mW
T <sub>stg</sub>	Storage Temperature		-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V	
V <sub>in</sub>	DC Input Voltage	0	5.5	V	
V <sub>out</sub>	DC Output Voltage		0	$V_{CC}$	V
T <sub>A</sub>	Operating Temperature		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V <sub>0</sub> (Figure 3) V	$_{CC} = 3.3 \text{ V} \pm 0.3 \text{V}$ $_{CC} = 5.0 \text{ V} \pm 0.5 \text{V}$	0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature (°C)	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

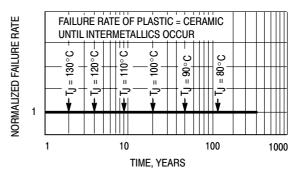


Figure 5. Failure Rate vs. Time Junction Temperature

# DC ELECTRICAL CHARACTERISTICS

			Vcc	Т	T <sub>A</sub> = 25°C		T <sub>A</sub> = ≤ 85°C		T <sub>A</sub> = ≤ 125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
V <sub>IN</sub> = V <sub>IH</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μА
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$ )

			Т	T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40	$T_A = -40 \text{ to } 85^{\circ}\text{C}$ $T_A = -55 \text{ to } 125^{\circ}\text{C}$		to 125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub> Maximum Propagation Delay, A to Y $V_{CC} = 3.3 \pm 0.3 \text{ VC}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$			7.2 9.7	11.0 14.5	1.0 1.0	13.0 16.5	1.0 1.0	13.0 16.5	ns	
	7.01	$V_{CC} = 5.0 \pm 0.5 \text{ VC}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		5.0 6.5	7.2 9.2	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E to Y	$V_{CC} = 3.3 \pm 0.3 \text{ VC}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		6.4 8.9	9.2 12.7	1.0 1.0	11.0 14.5	1.0 1.0	11.0 14.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ VC}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		4.4 5.9	6.3 8.3	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (1)	26	pF

<sup>1.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/2 (per decoder). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **SWITCHING WAVEFORMS**

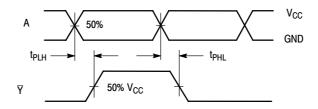


Figure 6.

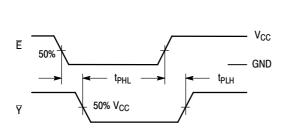
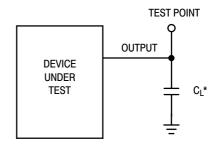


Figure 7.



\*Includes all probe and jig capacitance

Figure 8. Test Circuit

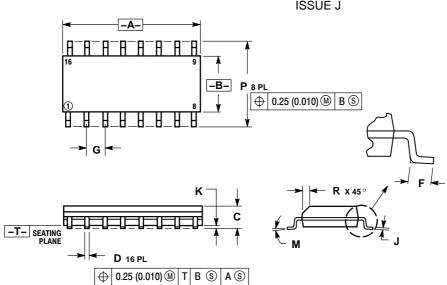
# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHC139D	SOIC-16	48 Units / Rail
MC74VHC139DR2	SOIC-16	2500 / Tape & Reel
MC74VHC139DR2G SOIC-16 (Pb-Free)		2500 / Tape & Reel
MC74VHC139DT	TSSOP-16	96 Units / Rail
MC74VHC139DTR2	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
MC74VHC139M	SOEIAJ-16	50 Units / Rail

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS



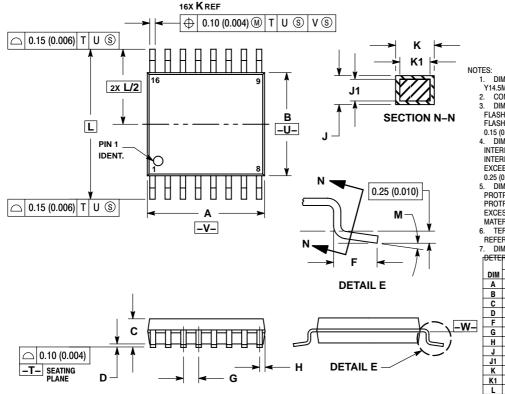


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	M 0° 7°		0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

## TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



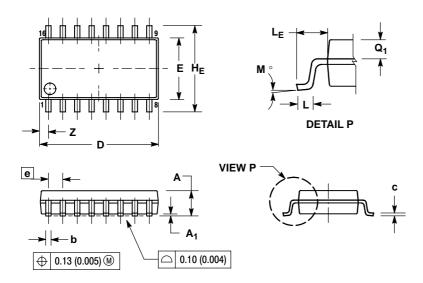
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE

DETE	RMINED /	AT DATUN	PLANE -W		
	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
M	0°	8°	0°	8°	

#### PACKAGE DIMENSIONS

## SOEIAJ-16 M SUFFIX CASE 966-01 ISSUE O



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE
   MOLD FLASH OR PROTRUSIONS AND ARE
   MEASURED AT THE PARTING LINE. MOLD FLASH
   OR PROTRUSIONS SHALL NOT EXCEED 0.15
   (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	-	2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.78		0.031

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